

# M74HC4316

# QUAD BILATERAL SWITCH

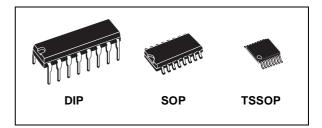
- HIGH SPEED: t = 12pc (TVP)
- t<sub>PD</sub> = 13ns (TYP.) at V<sub>CC</sub> = 6V ■ LOW POWER DISSIPATION:
- $I_{CC} = 1\mu A(MAX.)$  at  $V_{cc} = 5V$
- LOW "ON" RESISTANCE: 120Ω TYP. (V<sub>CC</sub> - V<sub>EE</sub> = 2V) 50Ω TYP. (V<sub>CC</sub> - V<sub>EE</sub> = 4.5V) 35Ω TYP. (V<sub>CC</sub> - V<sub>EE</sub> = 9V)
- WIDE ANALOG INPUT VOLTAGE RANGE ± 6v
- LOW CROSSTALK BETWEEN SWITCHES
- FAST SWITCHING
- SINE WAVE DISTORTION:
- 0.020 at V<sub>CC</sub> V<sub>EE</sub> = 9V ■ HIGH NOISE IMMUNITY:
- $V_{\text{NIH}} = V_{\text{NIL}} = 28 \% V_{\text{CC}} (\text{MIN.})$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 4316

### DESCRIPTION

The M74HC4316 is an high speed CMOS QUAD BILATERAL SWITCH fabricated with silicon gate  $C^2MOS$  technology.

This device has four independent analogue switches. Each switch has two input/output terminals (nI/O, nO/I) and an active high select input (nC).

#### PIN CONNECTION AND IEC LOGIC SYMBOLS

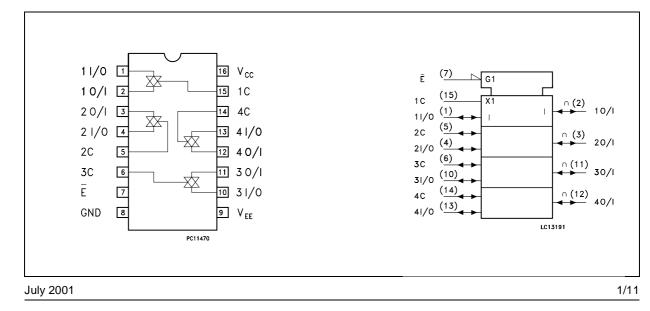


#### **ORDER CODES**

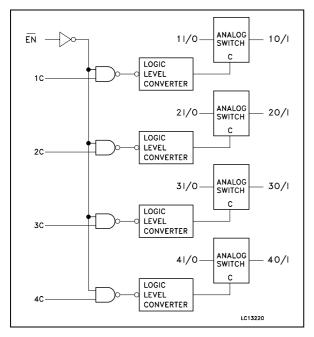
PACKAGE	TUBE	T & R				
DIP	M74HC4316B1R					
SOP	M74HC4316M1R	M74HC4316RM13TR				
TSSOP		M74HC4316TTR				

When the enable input is high, all four analog switches are off. The supply voltage for the digital signals applied to  $V_{CC}$  and GND must be whitin the range 0 to 6 V. The voltage swing on the analogue Inputs/Outputs can be between  $V_{CC}$  (positive limit) and  $V_{EE}$  (negative limit). The voltage between  $V_{CC}$  and  $V_{EE}$  must not exceed 12V.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.



## LOGIC DIAGRAM



### **ABSOLUTE MAXIMUM RATINGS**

### **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 10, 13	1 to 4 I/O	Independent Inputs/Out- puts
2, 3, 11, 12	1 to 4 O/I	Independent Outputs/ Inputs
7	Ē	Enable Inputs (Active LOW)
15, 5, 6, 14	1C to 4C	Enable Inputs (Active High)
9	$V_{EE}$	Negative Supply Voltage
8	GND	Ground (0V)
16	V <sub>CC</sub>	Positive Supply Voltage

#### **TRUTH TABLE**

Ē	С	SWITCH FUNCTION
L	Н	ON
L	L	OFF
Н	Х	OFF

57

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
$V_{CC}$ - $V_{EE}$	Supply Voltage	-0.5 to +13	V
VI	Control Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>I/O</sub>	Switch Input/Output Voltage	V <sub>EE</sub> -0.5 to V <sub>CC</sub> + 0.5	V
۱ <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
Ι <sub>Ο</sub>	DC Output Source Sink Current Per Output Pin	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
PD	Power Dissipation	500(*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied (\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Value	Unit	
V <sub>CC</sub>	Supply Voltage		2 to 12	V	
$V_{EE}$	Supply Voltage		-6 to 0	V	
$V_{CC}$ - $V_{EE}$	Supply Voltage		2 to 12	V	
VI	Input Voltage	0 to V <sub>CC</sub>	V		
V <sub>I/O</sub>	Switch I/O Voltage		0 to V <sub>CC</sub>	V	
T <sub>op</sub>	Operating Temperature		-55 to 125	°C	
	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000		
t <sub>r</sub> , t <sub>f</sub>		$V_{CC} = 4.5V$	0 to 500	ns	
		$V_{CC} = 6.0V$	0 to 400		

# DC SPECIFICATIONS

		Test Condition						Value				
Symbol	Parameter	v <sub>cc</sub>	V <sub>EE</sub>		т	T <sub>A</sub> = 25°C		-40 to 85°C		-55 to 125°C		Unit
		(Ŭ)	(⊽)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>IHC</sub>	High Level	2.0			1.5			1.5		1.5		
	Control Input	4.5			3.15			3.15		3.15		V
Voltage	6.0			4.2			4.2		4.2			
V <sub>ILC</sub>	Low Level Control	2.0					0.5		0.5		0.5	
	Input Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
R <sub>ON</sub>	ON Resistance	4.5	GND	$V_{I} = V_{IHC}$		70	170		200			
		4.5	-4.5	$V_{I/O} = V_{CC}$ to $V_{EE}$		50	85		105			
		6.0	-6.0	I <sub>I/O</sub> = 0.1mA		30	70		85			
		2.0	GND			120	180		215			Ω
		4.5	GND	$V_I = V_{IHC}$ $V_{I/O} = V_{CC} \text{ or } V_{EE}$		50	80		100			
		4.5	-4.5	$I_{I/O} = 0.1 \text{ mA}$		35	60		75			
		6.0	-6.0	1/0 - 0. 111/1		20	40		60			
$\Delta R_{ON}$	Difference of ON	4.5	GND	$V_{IN} = V_{IHC} \text{ or } V_{ILC}$		10	15		20			
	Resistance	4.5	-4.5	$V_{I/O} = V_{CC}$ to $V_{EE}$		5	10		15			Ω
	between switches	6.0	-6.0	I <sub>I/O</sub> = 0.1mA		5	10		15			
I <sub>OFF</sub>	Input/Output	6.0	GND	$V_{OS} = V_{CC}$ or GND			±0.06		$\pm 0.6$		± 2	
	Leakage Current (SWITCH OFF)	6.0	-6.0	$V_{IS} = V_{CC} \text{ or } GND$ $V_{IN} = V_{IHC} \text{ or } V_{ILC}$			± 0.1		± 1		± 2	μA
I <sub>IZ</sub>	Switch Input	6.0	GND				±0.06		± 0.6		± 2	μΑ
	Leakage Current (SWITCH ON, OUTPUT OPEN)	6.0	-6.0	$V_{OS} = V_{CC} \text{ or } GND$ $V_{IN} = V_{IHC} \text{ or } V_{ILC}$			± 0.1		± 1		± 2	
I <sub>IN</sub>	Control Input Current	6.0	V	I = V <sub>CC</sub> or GND		10 <sup>-5</sup>	± 0.1		± 1		± 1	μA



			Test	Condition				Value				
Symbol	Parameter	v <sub>cc</sub>	V <sub>EE</sub>	V <sub>EE</sub>		T <sub>A</sub> = 25°C			85°C	-55 to	125°C	Unit
		(V)	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
$\Phi_{I/O}$	Phase Difference	2.0	GND			12	30		40			
	Between Input	4.5	GND			3	6		8			
and Output	6.0	GND			3	5		7			ns	
	4.5	-4.5			2	4		5				
	6.0	-6.0			2	4		5				
t <sub>PZL</sub> Output Enable	2.0	GND			56	115		145				
t <sub>PZH</sub>	Time	4.5	GND			14	23		29			
	(E, C - OUT)	6.0	GND	$R_L = 1K\Omega$		12	20		25			ns
		4.5	-4.5			13	21		26			
		6.0	-6.0			11	18		23			
t <sub>PLZ</sub>	Output Disable	2.0	GND			112	205		255			
t <sub>PHZ</sub>	Time	4.5	GND			28	41		51			
	(Ē, C - OUT)	6.0	GND	$R_L = 1K\Omega$		24	35		43			ns
		4.5	-4.5			24	34		43			
		6.0	-6.0			21	29		36			
f <sub>MAX</sub>	Maximum Control	2.0	GND	$R_L = 1K\Omega$		2						
	Input Frequency	4.5	GND	C <sub>L</sub> = 15 pF		9						MHz
		6.0	GND	$V_{OUT} = 1/2 V_{CC}$		11						

# **AC ELECTRICAL CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ns}$ )

# **CAPACITIVE CHARACTERISTICS**

		Test Condition		Value							
Symbol	Parameter	v <sub>cc</sub>			T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C	
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance				5	10		10		10	pF
C <sub>I/O</sub>	Switch Terminal Capacitance	4.5	-4.5		5						pF
C <sub>IOS</sub>	Feed Through Capacitance	4.5	-4.5		1						pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	5.0	GND		16						pF

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$ 

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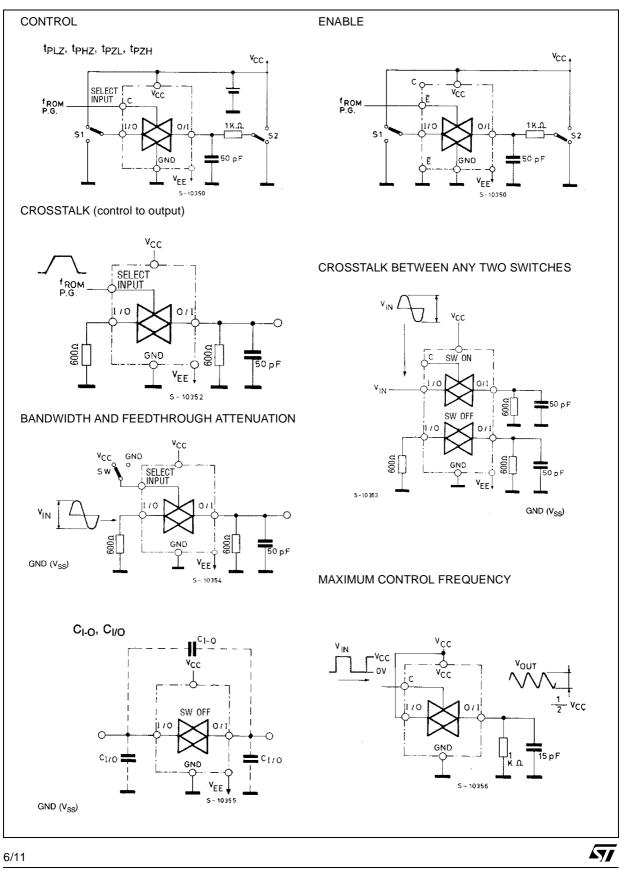
Symbol	Parameter				Test Condition	Value	Unit
		V <sub>CC</sub> (V)	V <sub>EE</sub> (V)	V <sub>IN</sub> (V <sub>p-p</sub> )		Тур.	
	Sine Wave	2.25	2.25	4		0.025	
	Distortion (THD)	4.5	4.5	8	f <sub>IN</sub> = 1 KHz R <sub>L</sub> = 10 KΩ, C <sub>L</sub> = 50 pF	0.020	%
		6.0	6.0	11		0.018	
f <sub>MAX</sub>	Frequency	2.25	2.25		Adjust f <sub>IN</sub> voltage to obtain 0 dBm at V <sub>OS</sub> .	28	
	Response	4.5	4.5 Increase f <sub>IN</sub> Frequency until dB meter reads -3dB		42	MHz	
	(Switch ON)	6.0	6.0		$R_L = 50\Omega$ , $C_L = 10$ pF, $f_{IN} = 1$ MHz sine wave	43	
	Feed through	2.25	2.25		$V_{IN}$ is centered at $V_{CC}/2$ . Adjust input for 0 dBm	-50	
	Attenuation	4.5	4.5		$R_L = 600\Omega$ , $C_L = 50 \text{ pF}$ , $f_{IN} = 1 \text{MHz}$ sine wave	-50	dB
	(Switch OFF)	6.0	6.0			-50	
	Crosstalk (Control	2.25	2.25				
	Input to Signal	4.5	4.5	$R_L = 6$	00 $\Omega$ , C <sub>L</sub> = 50 pF, f <sub>IN</sub> = 1MHz square wave (t <sub>r</sub> = t <sub>f</sub> =6ns)	5	mV
	Output)	6.0	6.0				
	Crosstalk	2.25	2.25		Adjust V <sub>IN</sub> to Obtain 0 dBm at input	-50	
	(Between Any	4.5	4.5	$R_L = 600\Omega$ , $C_L = 50 \text{ pF}$ , $f_{IN} = 1 \text{MHz}$ sine wave			dB
	Switches)	6.0	6.0	1		-50	1

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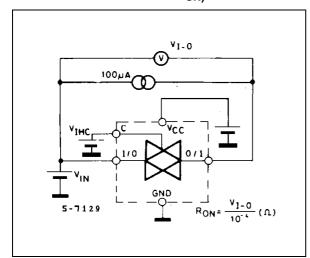
# ANALOG SWITCH CHARACTERISTICS (GND = 0V;T\_A = 25°C)



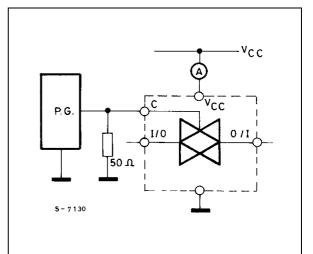
# SWITCHING CARACTERISTICS TEST CIRCUIT



# CHANNEL RESISTANCE (R<sub>ON)</sub>



I<sub>CC</sub> (Opr.)



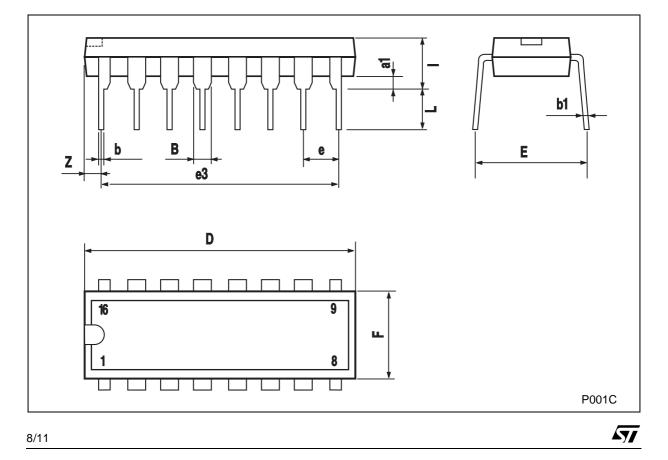


# M74HC4316

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	Plastic DIP-16 (0.25) MECHANICAL DATA										
DIM.		mm.		inch							
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.					
a1	0.51			0.020							
В	0.77		1.65	0.030		0.065					
b		0.5			0.020						
b1		0.25			0.010						
D			20			0.787					
E		8.5			0.335						
е		2.54			0.100						
e3		17.78			0.700						
F			7.1			0.280					
I			5.1			0.201					
L		3.3			0.130						
Z			1.27			0.050					

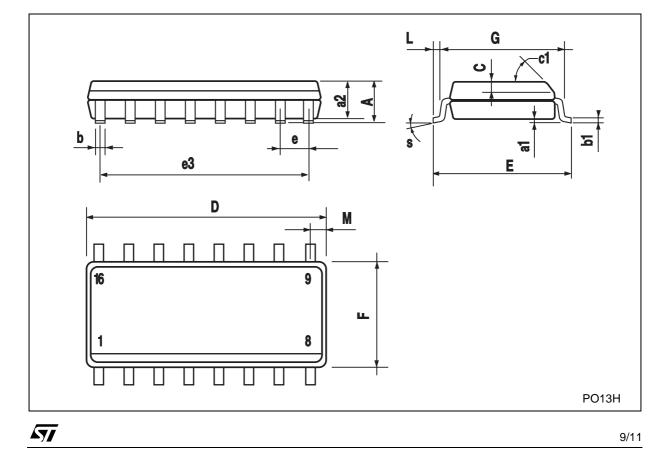
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# Downloaded from Arrow.com.

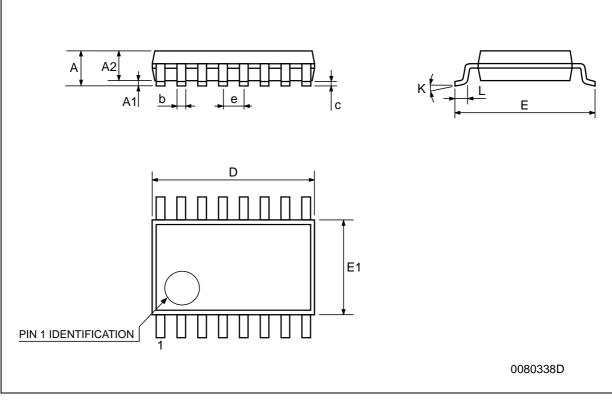
DIM.		mm.			inch	
DINI.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1		•	45°	(typ.)	•	
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.62			0.024





# M74HC4316

	TSSOP16 MECHANICAL DATA										
DIM.		mm.		inch							
Diwi.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.					
А			1.2			0.047					
A1	0.05		0.15	0.002	0.004	0.006					
A2	0.8	1	1.05	0.031	0.039	0.041					
b	0.19		0.30	0.007		0.012					
С	0.09		0.20	0.004		0.0089					
D	4.9	5	5.1	0.193	0.197	0.201					
E	6.2	6.4	6.6	0.244	0.252	0.260					
E1	4.3	4.4	4.48	0.169	0.173	0.176					
е		0.65 BSC			0.0256 BSC						
К	0°		8°	0°		8°					
L	0.45	0.60	0.75	0.018	0.024	0.030					



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